

ABSTRACT OF DISCLOSURE

A heterojunction bipolar transistor includes an emitter layer, a base layer and a collector layer laminated on a top surface of a semiconductor substrate, and a heat sink layer made of a metal and provided on a rear surface of the substrate. A via hole is cut through the emitter layer, the base layer, the collector layer and the substrate. A surface electrode of the emitter layer and the heat sink layer are connected to each other by a metal wiring line running through within the via hole, which is capable of improving the heat radiation and reducing the emitter inductance.